

DESCRIPTION The 2SC945 is designed for use in driver stage of AF amplifier and low speed switching.

FEATURES

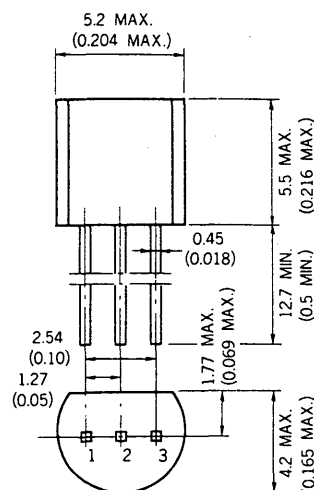
- High Voltage LV_{CEO} : 50 V MIN.
- Excellent h_{FE} Linearity h_{FE1} (0.1 mA)/ h_{FE2} (1.0 mA) : 0.92 TYP.

ABSOLUTE MAXIMUM RATINGS

Maximum Temperatures	
Storage Temperature	-55 to +125 °C
Junction Temperature	+125 °C Maximum
Maximum Power Dissipation (Ta = 25 °C)	
Total Power Dissipation	250 mW
Maximum Voltages and Currents (Ta = 25 °C)	
V _{CBO} Collector to Base Voltage	60 V
V _{CEO} Collector to Emitter Voltage	50 V
V _{EBO} Emitter to Base Voltage	5.0 V
I _C Collector Current	100 mA
I _B Base Current	20 mA

PACKAGE DIMENSIONS

in millimeters (inches)



1. EMITTER EIAJ : SC 43B
2. COLLECTOR JEDEC : TO 92
3. BASE IEC : PA33

ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

SYMBOL	CHARACTERISTIC	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
h_{FE1}	DC Current Gain	50	185			V _{CE} =6.0 V, I _C =0.1 mA
h_{FE2}	DC Current Gain	90	200	600		V _{CE} =6.0 V, I _C =1.0 mA
NF	Noise Figure		0.8	15	dB	V _{CE} =6.0 V, I _C =0.1 mA, R _G =2.0 kΩ, f=1.0 kHz
f _T	Gain Bandwidth Product	150	250	450	MHz	V _{CE} =6.0 V, I _E =-10 mA
C _{ob}	Collector to Base Capacitance		3.0	4.0	pF	V _{CB} =6.0 V, I _E =0, f=1.0 MHz
I _{CBO}	Collector Cutoff Current			100	nA	V _{CB} =60 V, I _E =0
I _{EBO}	Emitter Cutoff Current			100	nA	V _{EB} =5.0 V, I _C =0
V _{BE}	Base to Emitter Voltage	0.55	0.62	0.65	V	V _{CE} =6.0 V, I _C =1.0 mA
V _{CE(sat)}	Collector Saturation Voltage		0.15	0.3	V	I _C =100 mA, I _B =10 mA
V _{BE(sat)}	Base Saturation Voltage		0.86	1.0	V	I _C =100 mA, I _B =10 mA

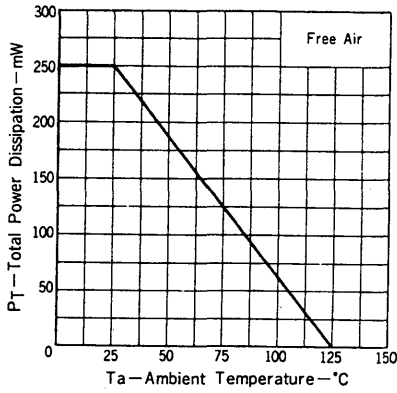
Classification of h_{FE2}

Rank	R	Q	P	K
Range	90 - 180	135 - 270	200 - 400	300 - 600

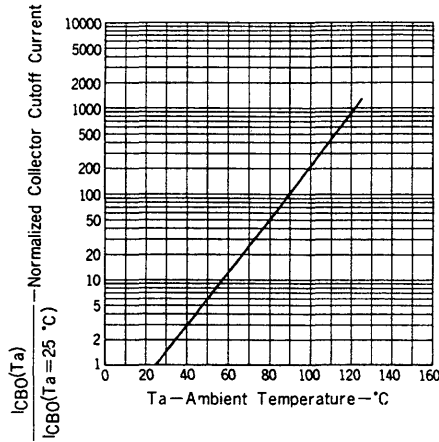
h_{FE2} Test Conditions : V_{CE} = 6.0 V, I_C = 1.0 mA

TYPICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$ unless otherwise noted)

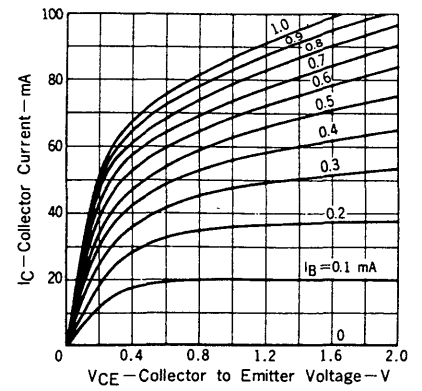
TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE



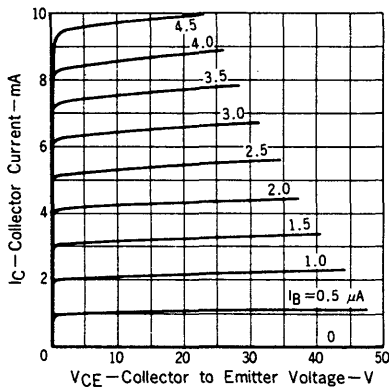
NORMALIZED COLLECTOR CUTOFF CURRENT vs. AMBIENT TEMPERATURE



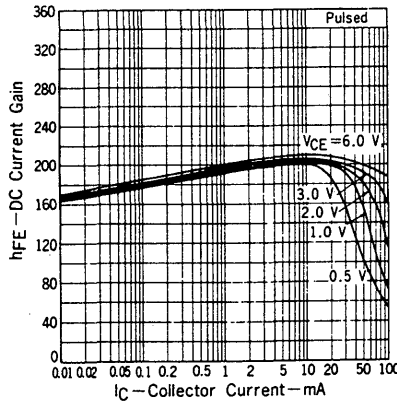
COLLECTOR CURRENT vs. COLLECTOR TO EMITTER VOLTAGE



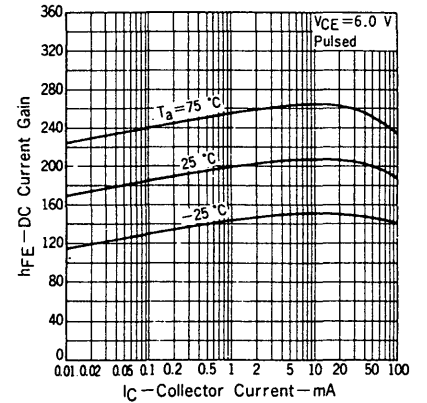
COLLECTOR CURRENT vs. COLLECTOR TO EMITTER VOLTAGE



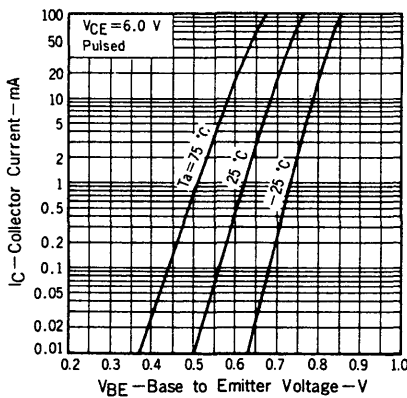
DC CURRENT GAIN vs. COLLECTOR CURRENT



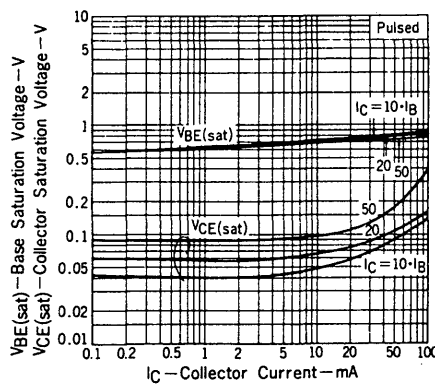
DC CURRENT GAIN vs. COLLECTOR CURRENT



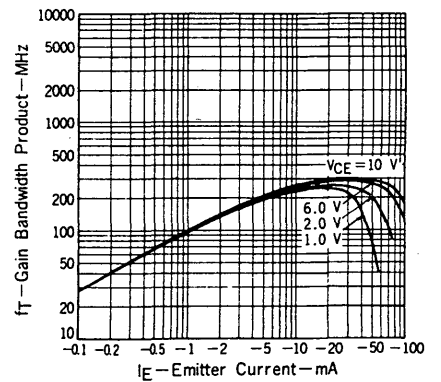
COLLECTOR CURRENT vs. BASE TO EMITTER VOLTAGE



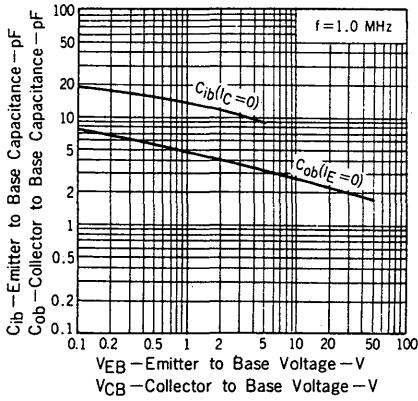
COLLECTOR AND BASE SATURATION VOLTAGE vs. COLLECTOR CURRENT



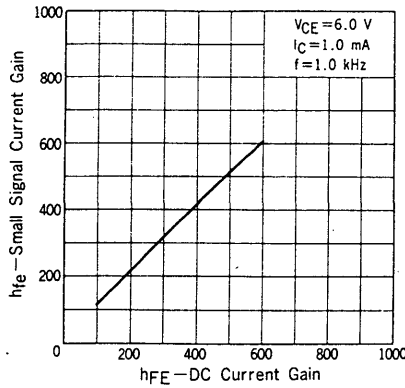
GAIN BANDWIDTH PRODUCT vs. EMITTER CURRENT



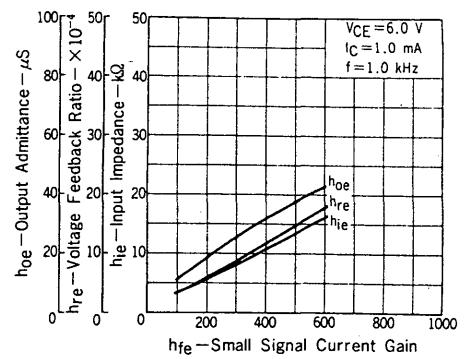
EMITTER TO BASE AND COLLECTOR TO BASE CAPACITANCE vs. REVERSE VOLTAGE



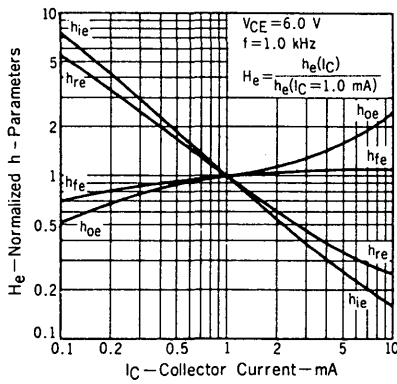
SMALL SIGNAL CURRENT GAIN vs. DC CURRENT GAIN



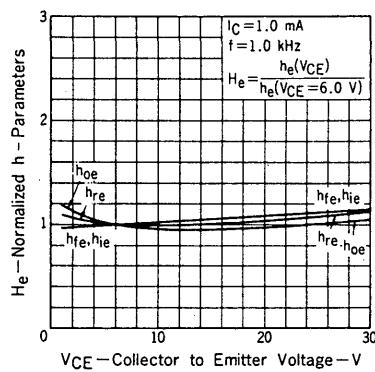
INPUT IMPEDANCE, VOLTAGE FEEDBACK RATIO AND OUTPUT ADMITTANCE vs. SMALL SIGNAL CURRENT GAIN



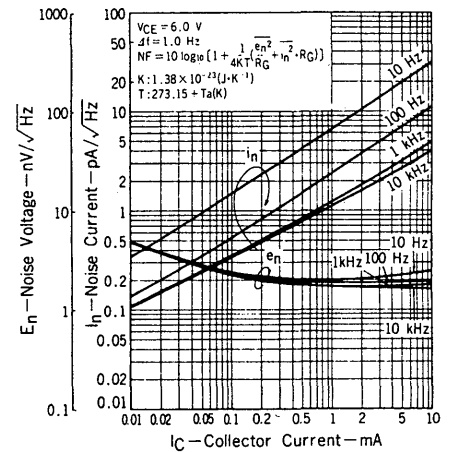
NORMALIZED h-PARAMETERS vs. COLLECTOR CURRENT



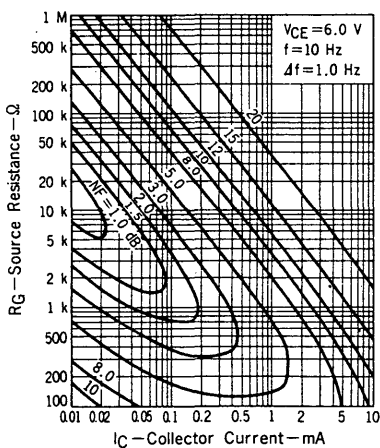
NORMALIZED h-PARAMETERS vs. COLLECTOR TO EMITTER VOLTAGE



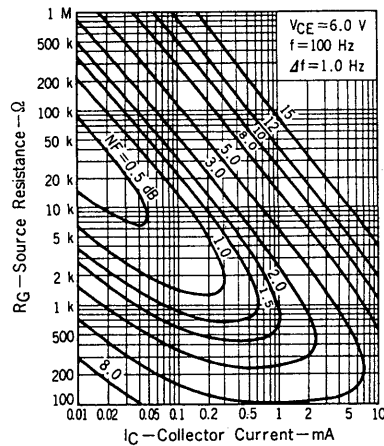
En AND In vs. COLLECTOR CURRENT



NOISE FIGURE MAP 1



NOISE FIGURE MAP 2



NOISE FIGURE MAP 3

